



NPN BUX12

HIGH CURRENT, HIGH SPEED , HIGH POWER TRANSISTOR

The BUX12 is silicon multiepitaxial planar NPN transistors in Jedec TO-3. They are intended for use in switching and linear applications in military and industrial equipment.
Compliance to RoHS

ABSOLUTE MAXIMUM RATINGS

Symbol			Unit
V_{CEO}	Collector-Emitter Voltage	$I_B = 0$	250 V
V_{CBO}	Collector-Base Voltage	$I_E = 0$	300 V
V_{EBO}	Emitter-Base Voltage	$I_C = 0$	7.0 V
V_{CEX}	Collector-Emitter Voltage	$V_{BE} = -1.5V$	300 V
I_C	Collector Current		20 A
I_{CM}	Collector Peak Current	$t_p = 10ms$	25 A
I_B	Base Current		4 A
P_t	Total Power Dissipation	@ $T_C = 25^\circ$	150 W
T_J	Junction Temperature		200 °C
T_{Stg}	Storage Temperature		-65 to +200 °C

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJC}	Thermal Resistance, Junction to Case	1.17	°C/W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

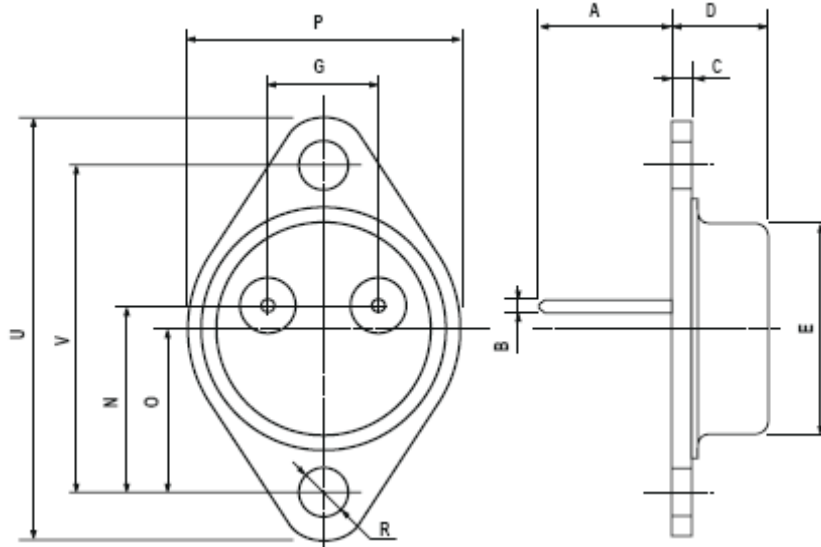
Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
$V_{CE0(SUS)}$	Collector-Emitter Sustaining Voltage (*)	$I_C=200\text{ mA}$	250	-	-	V
$V_{EB0(SUS)}$	Emitter-Base Breakdown Voltage (*)	$I_C=0\text{A}, I_E=50\text{ mA}$	7	-	-	V
I_{CEO}	Collector Cutoff Current	$V_{CE}=200\text{ V}, I_B=0\text{A}$	-	-	1.5	mA
I_{CEX}	Collector Cutoff Current	$V_{CE}=V_{CEX}, V_{BE}=-1.5\text{V}$	-	-	1.5	mA
		$V_{CE}=V_{CEX}, V_{BE}=-1.5\text{V}$ $T_{case}=125^\circ\text{C}$	-	-	6	
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5.0\text{ V}, I_C=0$	-	-	1	mA
h_{FE}	DC Current Gain (*)	$I_C=5\text{ A}, V_{CE}=4.0\text{ V}$	20	-	60	-
		$I_C=10\text{ A}, V_{CE}=4.0\text{ V}$	10	-	-	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=5\text{ A}, I_B=0.5\text{ A}$	-	0.22	1	V
		$I_C=10\text{ A}, I_B=1.25\text{ A}$	-	0.5	1.5	
$V_{BE(SAT)}$	Base-Emitter saturation Voltage (*)	$I_C=10\text{ A}, I_B=1.25\text{ A}$	-	1.23	1.5	
$I_{S/B}$	Second breakdown collector current	$V_{CE}=30\text{ V}, t_s=1\text{ s}$	5	-	-	A
		$V_{CE}=140, t_s=1\text{ s}$	0.15	-	-	
$E_{S/B}$	Clamped $E_{S/B}$ Collector current	$V_{clamp}=250\text{ V}, L=500\text{ }\mu\text{H}$	10	-	-	A
f_T	Transition frequency	$V_{CE}=15\text{ V}, I_C=1\text{ A}$ $f=10\text{ MHz}$	8	-	-	MHz
t_{on}	Turn-on time	$I_C=10\text{ A}, I_B=1.25\text{ A}$ $V_{CC}=150\text{ V}$	-	0.28	1	μs
t_s	Storage time	$I_C=10\text{ A}, V_{CC}=150\text{ V}$	-	1.45	2	
t_f	File time	$I_{B1}=-I_{B2}=1.25\text{ A}$	-	0.23	0.5	

(*) Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

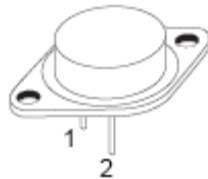
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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